



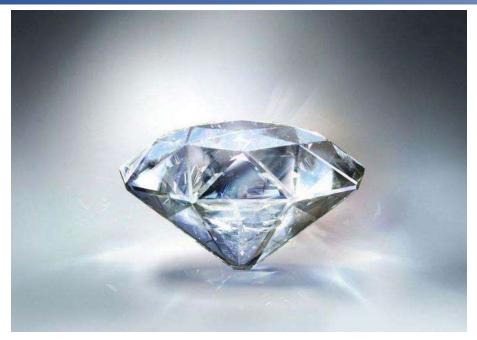
# Diamond Semiconductor: "deep elastic strain engineering"

# Yang Lu

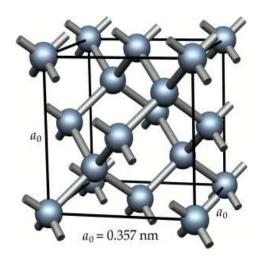
Department of Mechanical Engineering Department of Materials Science and Engineering

City University of Hong Kong

# Diamond as the hardest (tooling) material



#### Covalent bond, sp<sup>3</sup> hybridization



Drilling



(武汉) 转接拒据册班从和李大师教授团队参加 7部分结察方案设计和转挥横似证编等工作。为 "嫦娥"配上金丽站。采用表达码会。多点采标 的方式。设计了钻具钻散和机械粗赛取至两种"理 也"模式。超课材料助为图中编节!

Cutting



Grinding/polishing

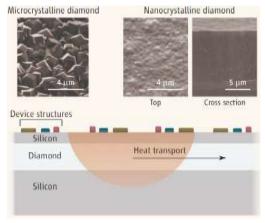


"harder than (natural) diamond..." --- YSU, JLU...

#### Also, "Mount Everest" of Electronic/Photonic Materials...

**Ultrawide bandgap semiconductor** with high thermal conductivity, dielectric breakdown strength, carrier mobility... (& NV center)

#### Si-diamond-Si integrated circuit

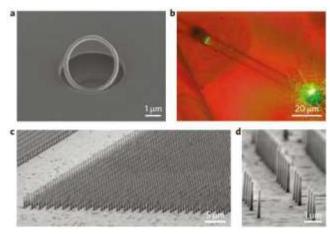


Science **319**, 1491 (2008)

# 

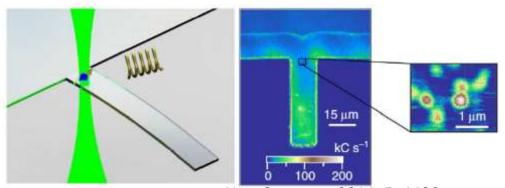
Sci. Adv. 2016, 2, e1600911

#### Diamond photonic structures



Nat. Photonics. 5, 397–405 (2011)

#### MEMS; Quantum Nanomechanical Resonator



*Nat. Commun.* 2014, 5, 4429

# **Ultimate Semiconductor for High Power/Frequency Applications**

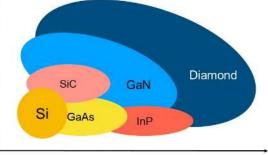




#### The properties that make diamond shine..

Parameters	Si	SiC	GaN	Diamond
Bandgap E <sub>g</sub> (eV)	1.11	3.26	3.39	5.47
Breakdown field E <sub>c</sub> (MV/cm)	0.3	3.5	3.4	10.0
Electron mobility $\mu_e$ (cm <sup>2</sup> /Vs)	1,500	800	900	2,200
Thermal conductivity (W/cmK)	1.5	4.9	2.2	21.3

POWER HANDLING



**Power Devices** 

OPERATING FREQUENCY



#### Moore's Law and Moving Beyond Silicon: The Rise of Diamond Technology

BUSINESS CULTURE GEAR IDEAS SCIENCE

SHARE

f SHARE

TWEET

COMMENT

✓ EMAIL

John Bardeen, William Shockley and Walter Brattain, the inventors of the transistor, 1948 -- the birth of Silicon Valley.

ARTNER CONTENT ADAM KHAN, AKHAN SEMICONDUCTOR

# MOORE'S LAW AND MOVING BEYOND SILICON: THE RISE OF DIAMOND TECHNOLOGY



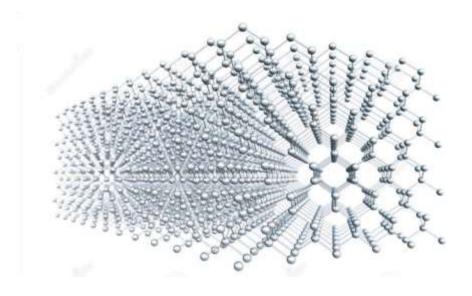
#### **Obstacle** in realization diamond electronics

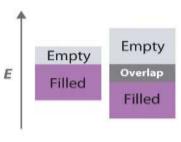
#### Doping for diamond is difficult, especially N type

Tight crystal lattice;

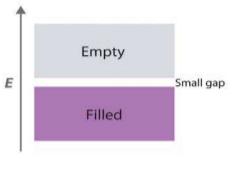
Small atomic number (limited doper);

Large bandgap energy...

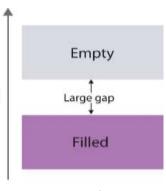






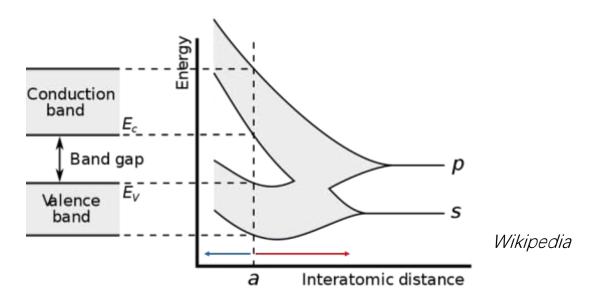




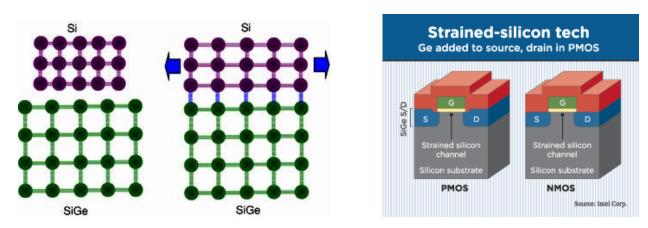


Insulator

# An alternative strategy --- elastic strain engineering



Applying lattice/elastic strain can considerably change the materials' properties!



http://www.eetimes.com/document.asp?doc\_id=1217259

# **Deform diamond elastically?**

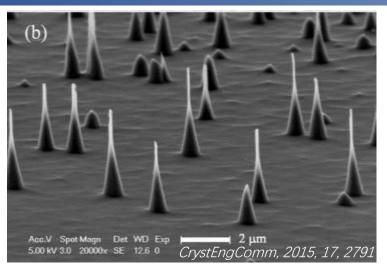
If you manage to deform a bulk diamond, it usually means you have broken it



Crazy Hidraulic Press <a href="https://youtu.be/YHU0aM9rCFA">https://youtu.be/YHU0aM9rCFA</a>

What about nanoscale?

#### Firstly, diamond nanoneedles --- from COSDAF Prof. WJ Zhang



# Micro-Raman Diamond needles Diamond film

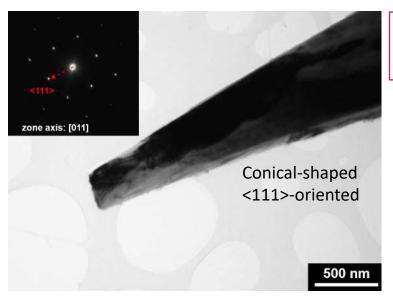
Raman Shift (cm<sup>-1</sup>)

1332 cm<sup>-1</sup>: sp<sup>3</sup> hybridized C-C bond structure

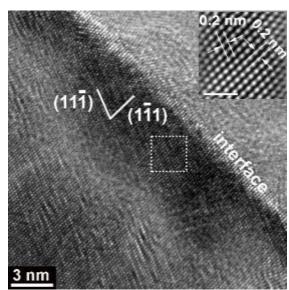
#### Plasma-induced etching of diamond thin films etching of diamond thin films

**HRTEM** 

**SAED** 

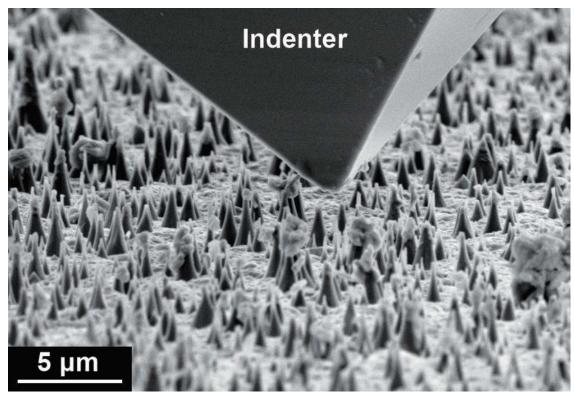


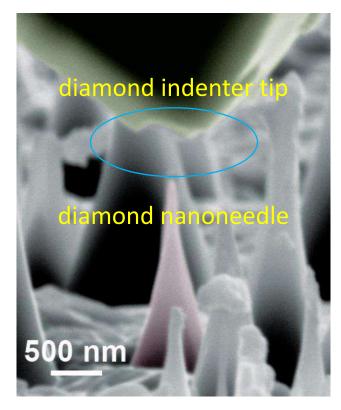
single-crystalline nanoneedles



Atomic-level smooth surface

#### **Experiment challenge:** using a nanoindenter, however...





shield VS. spear paradox...



Size effect

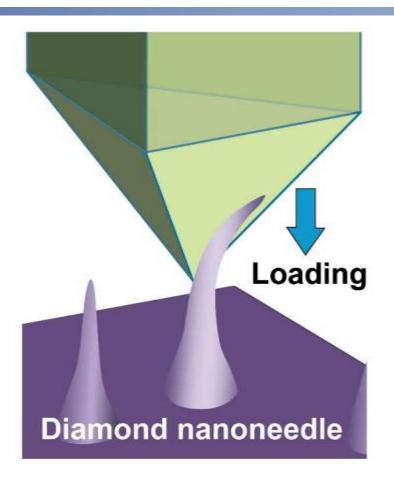
#### "Push-to-Bend" strategy

Quantitative force-displacement (F-D) data recorded;

in situ SEM imaging of real-time deformation geometry

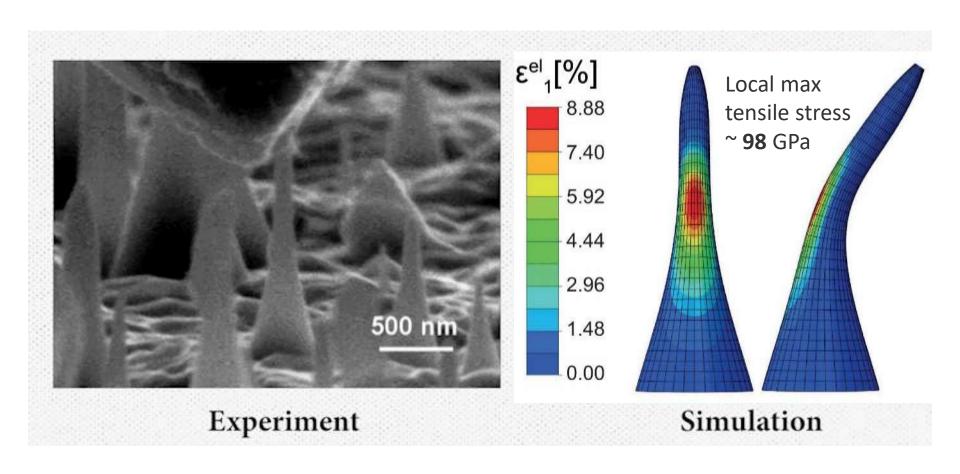


(From left: Dr. Hongti Zhang, Dr. Yang Lu and Mr. Amit Banerjee)



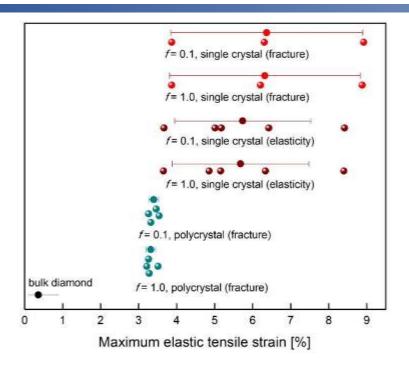
Push-to-Bend

#### Single-crystalline diamond nanoneedle: deep elastic bending



Bending of a single-crystalline diamond nanoneedle inside SEM, with fully recoverable flexural deformation

# Reducing size for enhanced elasticity



#### Science

Science **360** (6386), 300-302. DOI: 10.1126/science.aar4165

# Ultralarge elastic deformation of nanoscale diamond

Amit Banerjee, <sup>1,2+</sup> Daniel Bernoulli, <sup>3+</sup> Hongti Zhang, <sup>1,4+</sup> Muk-Fung Yuen, <sup>2,5</sup> Jiabin Liu, <sup>1</sup> Jichen Dong, <sup>6</sup> Feng Ding, <sup>6,7</sup> Jian Lu, <sup>1,4</sup> Ming Dao, <sup>3†</sup> Wenjun Zhang, <sup>2,5</sup>† Yang Lu, <sup>1,2,4</sup>† Subra Suresh <sup>8</sup>†

#### MATERIALS

# On the quest for the strongest materials

Diamond nanoneedles have strength approaching the theoretical maximum

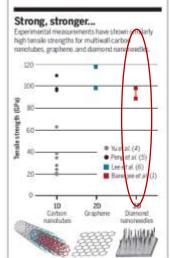
By Javier LLorea<sup>1,6</sup>

he strength of a material is a measure of its ability to withstand a load without breaking. Scientists in search of the strongest materials have recently turned their attention to nanomaterials, which have few of the defects that typically reduce a material's strength. On page 300 of this issue, Banerjee et al. (f) show that when nanoscale single-crystal diamond needles are elastically deformed, they fail at a maximum local tensile stress of ~89 to 98 GPa, which is very close to the theoretical limit for this material.

The maximum possible strength that a material can have in either tension or shear is controlled by the fracture of the interatomic bonds and is on the order of the interatomic bonds and is on the order of the control of the control

bond can be stretched to the theoretical limit. Maximum elastic tensile strains supported by bulk solids are between 0.2 and 0.4%, whereas tensile strains of up to 4% have been measured in micrometer-size whiskers (2). Recent progress in nanomaterial synthesis and nanomechanical testing has opened the possibility of probing the strength of material systems that are practically free of defects (3). In parallel, atomistic simulations based on densityfunctional theory and molecular dynamics can predict accurately the fracture strength of perfect crystals and allow the influence of defects and free surfaces on this property to be explored.

Because the carbon-carbon bond is the strongest in nature, the search for the strongest material has focused on onedimensional carbon nanotubes and twodimensional graphene nunoscale objects (see the figure). Experimental results and ab initio calculations indicate that the elastic modulus of carbon nanotubes and graphene is =1 TPa (4-6). The strengths measured in both types of nano-objects are thus very close to the theoretical limit (see the figure). By contrast, the reported tensile strength of bulk cubic diamond is much smaller (<10 GPa) (7). These differences in strength have been partially attributed to brittle fracture from defects during tensile deformation of bulk samples. Higher tensile strengths (up to 20 GPa) for diamond have been reported from Hertzian indentation tests (8), but these values must be treated with caution because of the uncertainties associated with the spherical indentation to determine the tensile strength. Regardless of the experimental technique, diamond fractures by cleavage along the (111) plane, which has the lowest fracture energy. The strengths reported by Banerice et al. (which correspond to a tensile strain of ~9%) are very close to the theoretical limit for diamond and to the maximum strength values reported for carbon nanotubes and gra-



VMOCA Materials Institute, Cristo Kendel Z. 20006 Getale. Machid, Spain. Department of Materials Science, Polytechnic University of Machid, E. J. C. de Ingeneros de Carriero, 28040 Machid, Spain. Etnal juster Uncadionales.org

### Allowing electronic property modulation through deep straining

# PNAS

# Deep elastic strain engineering of bandgap through machine learning

Zhe Shi<sup>a,b,1</sup>, Evgenii Tsymbalov<sup>c,1</sup>, Ming Dao<sup>a</sup>, Subra Suresh<sup>d,2</sup>, Alexander Shapeev<sup>c,2</sup>, and Ju Li<sup>a,b,2</sup>

"Department of Materials Science and Engineering, Massachusetts Institute of Technology, Cambridge, MA 02139; "Department of Nuclear Science Engineering, Massachusetts Institute of Technology, Cambridge, MA 02139; "Skolkovo Institute of Science and Technology, 121205 Moscow, Russia; and "Nanyang Technological University, 639798 Singapore, Republic of Singapore

Contributed by Subra Suresh, December 18, 2018 (sent for review November 1, 2018, reviewed by Yonggang Huang and Devendra K. Sadana)

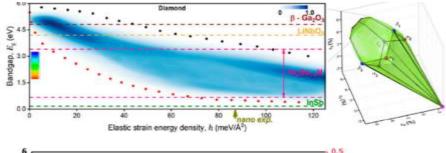
PHYSICAL REVIEW LETTERS 123, 195504 (2019)

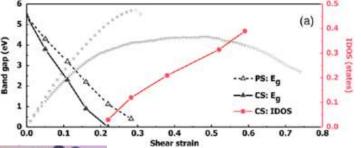
#### Smooth Flow in Diamond: Atomistic Ductility and Electronic Conductivity

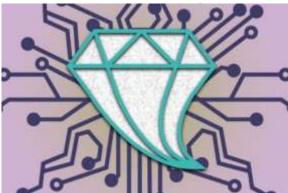
Chang Liu Q. Xianqi Songe, Quan Lio, 1.2 Yanming Moo, 1.2 and Changfeng Cheng State Key Laboratory of Superhard Materials. Key Laboratory of Automobile Moverials of MOE, Department of Materials Science, and Innovation Center for Computational Physics Method and Software. Jilin University, Changeline 130012. China International Course of Future Science. Jilin University. Changeline 130012. China

International Course of Future Science, Jilin University, Changelian 130012, China Department of Physics and Astronomy, University of Nevada, Lus Vegos, Nevada 89154, USA





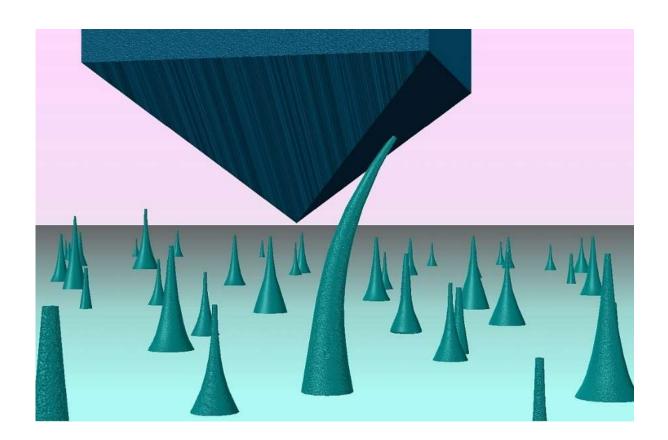




"These discoveries have opened up new avenues to explore how devices can be fabricated with even **more dramatic changes** in the materials' properties."

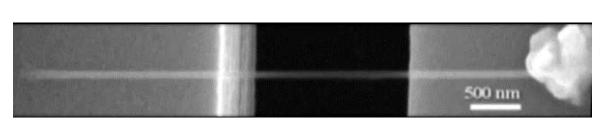
# Secondly, for real device application...

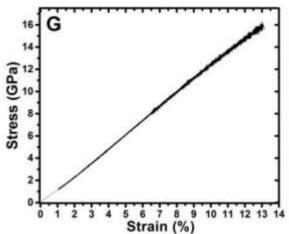
Device geometry; Straining method; Strain distribution...



#### **Tensile Elastic Straining of Silicon Nanowire**

#### 13% global deformation



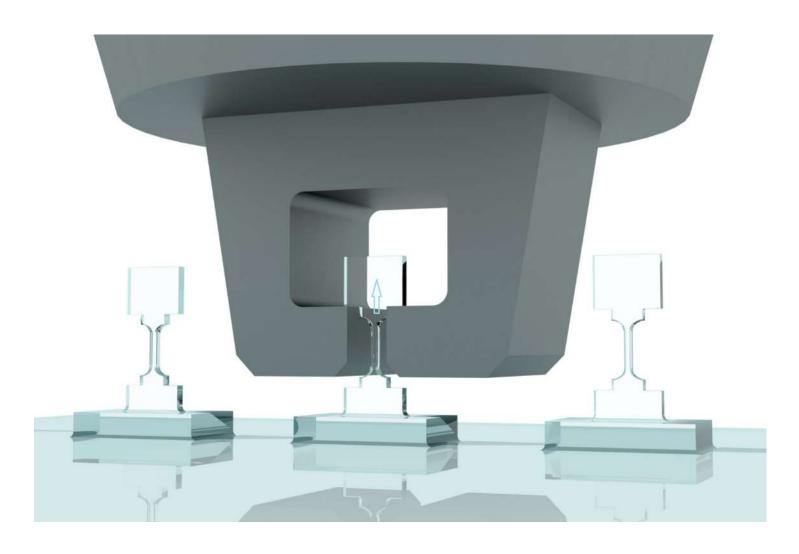


# **Science** Advances

Approaching the ideal elastic strain limit in silicon nanowires Hongti Zhang, Jerry Tersoff, Shang Xu, Huixin Chen, Qiaobao Zhang, Kaili Zhang, Yong Yang, Chun-Sing Lee, King-Ning Tu, Ju Li and Yang Lu (August 17, 2016) Sci Adv 2016, 2:.

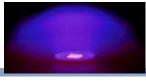
doi: 10.1126/sciadv.1501382

# So, new configuration...

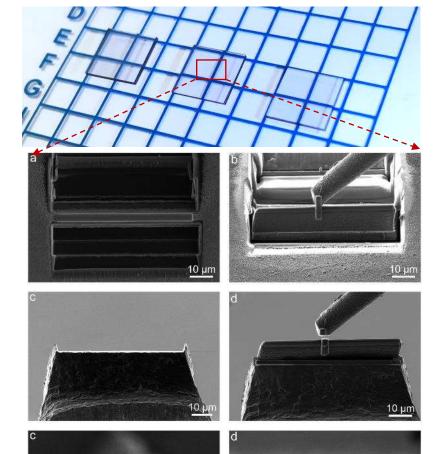


Uniaxial tensile straining of microfabricated diamond structures

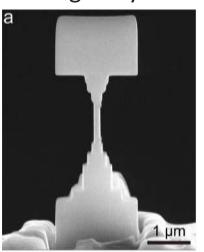
#### Microfabricated tensile specimen---by Bing Dai, Jiaqi Zhu @HIT



Sample fabrication process



Single crystalline diamond microbridge

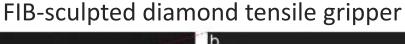


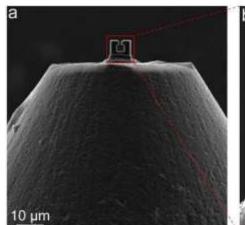
Thickness

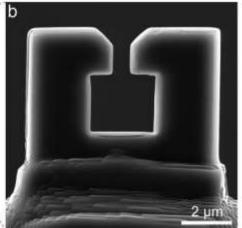
200 nm

Side view

Top view

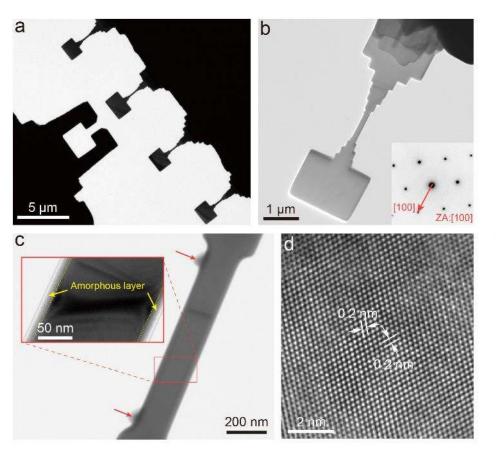




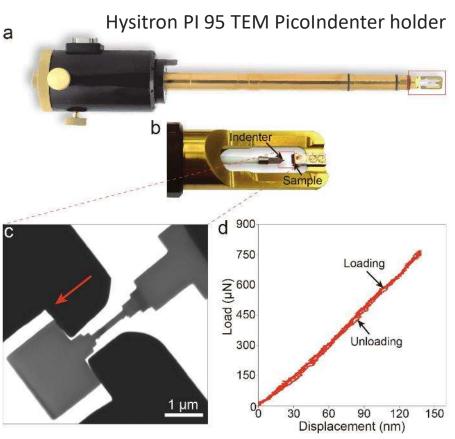


# in situ TEM tensile straining

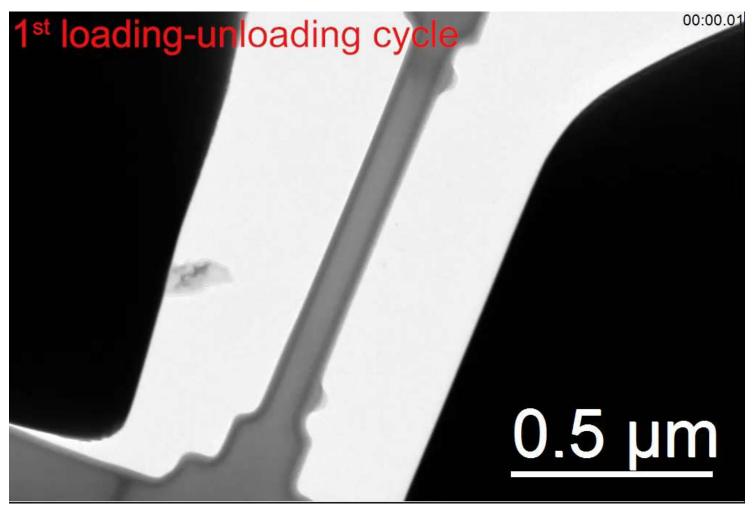
#### Sample characterization



#### in situ TEM tensile testing setup

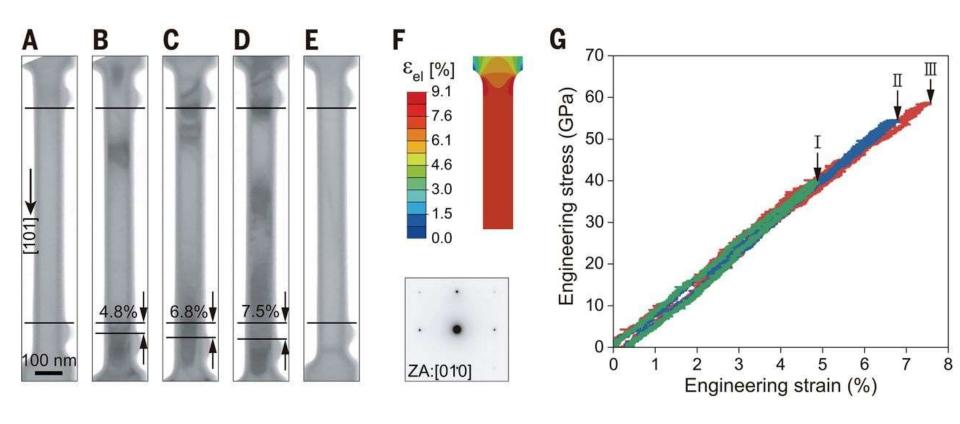


#### in situ Loading-unloading tensile straining



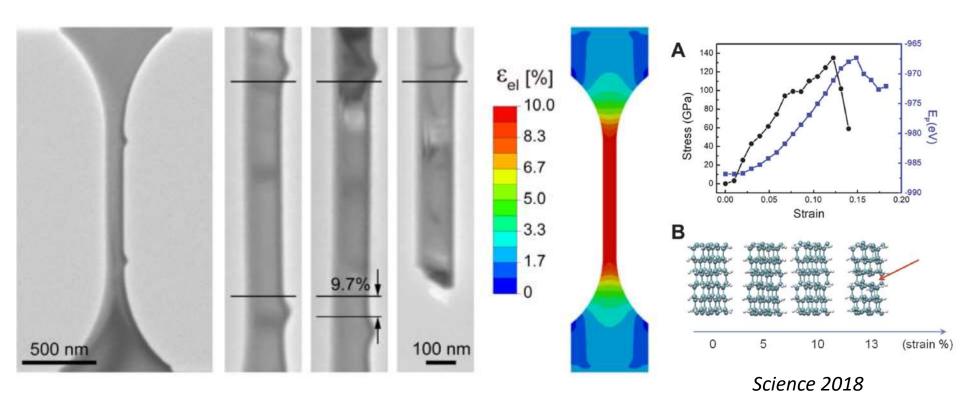
Loading-unloading cycles of a single-crystalline diamond bridge sample along [101] direction, with fully recoverable deformation (played at  $30 \times$  speed)

#### Ultralarge, uniform tensile elastic straining



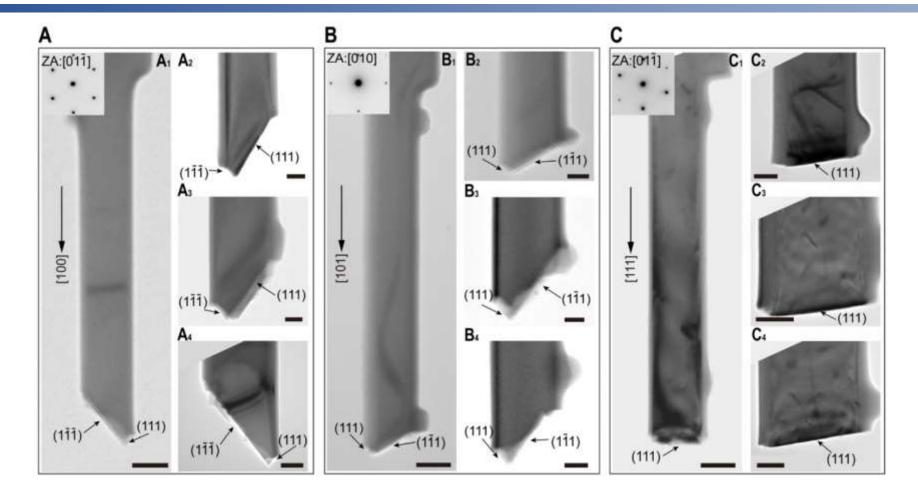
Large, uniform tensile elasticity in the microfabricated diamond bridge

### Optimization of sample geometry for extreme



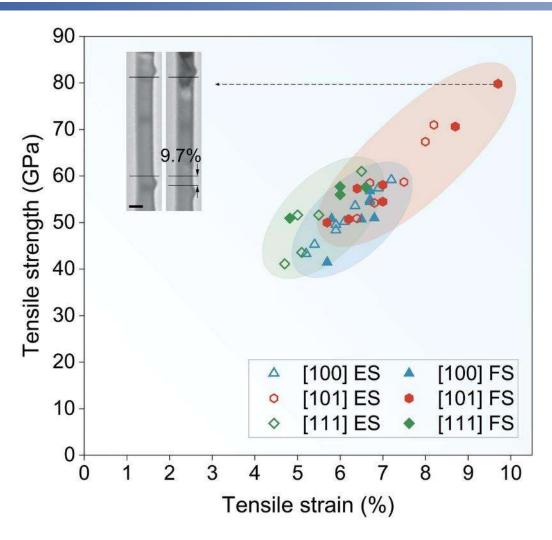
- Optimized by American Society for Testing and Materials (ASTM) standard
- Up to 10% sample-wide uniform elastic strain --- near ideal limit!

#### **Fracture morphologies**



- Without visible sign of plasticity during tensile deformation
- Retain the overall pristine single-crystalline structures
- Typical distinct {111} cleavage surfaces

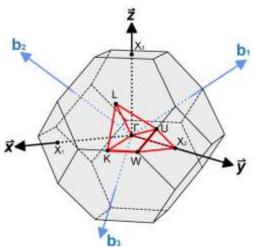
# **Experiment summary**



- ES: elastic strains from fully reversible runs; FS: failure-run strains
- 6-9% sample-wide elastic strains with full recovery

#### Lastly, electronic properties under deep elastic straining

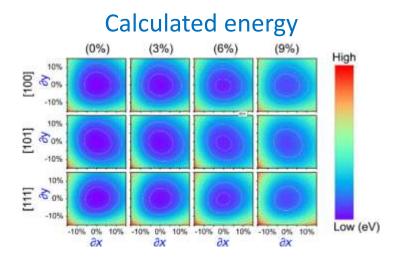
#### Brillouin zone of diamond primitive cell



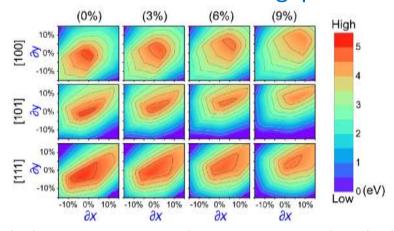
k-point coordinates of primitive cell

k-path: $\Gamma$ - $X_2$ - $U$ - $W$ - $K$ - $\Gamma$ - $L$ - $W$ - $X_2$					
symbol	$k_1$	$k_2$	<i>k</i> <sub>3</sub>		
Γ	0.000	0.000	0.000		
$X_2$	0.500	0.000	0.500		
U	0.625	0.250	0.625		
W	0.500	0.250	0.750		
K	0.375	0.375	0.750		
L	0.500	0.500	0.500		

-- DFT calculation by Andy Chou, JP Chou, Alice Hu

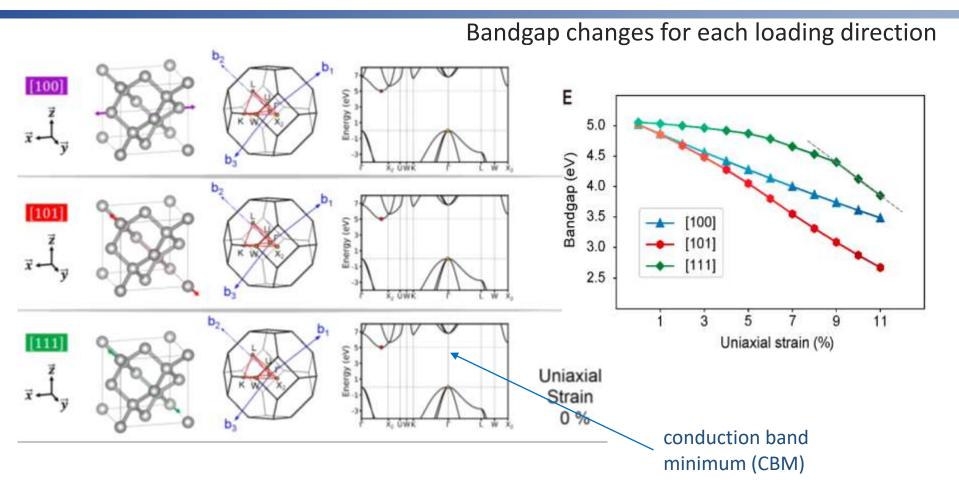


#### Calculated bandgap



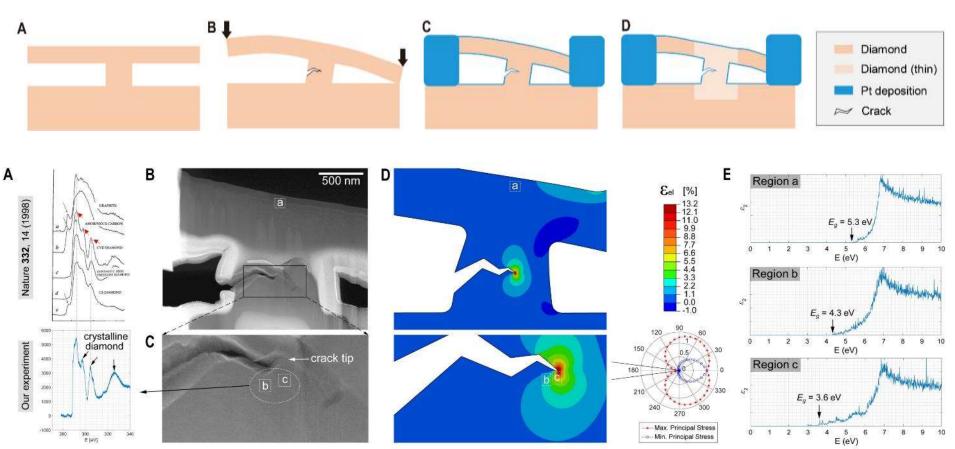
Diamond has small Poisson contraction and barely has transverse change on non-loaded axis

#### Band structure evolution upon tensile straining



- [101] direction with the **largest reduction** rate, down to ~3 eV at 9% strain → conventional wide-bandgap semiconductor
- Indirect-direct bandgap transition with tensile strains >9% along the [111] direction → optoelectronics

#### **EELS** characterization of strained diamond specimen

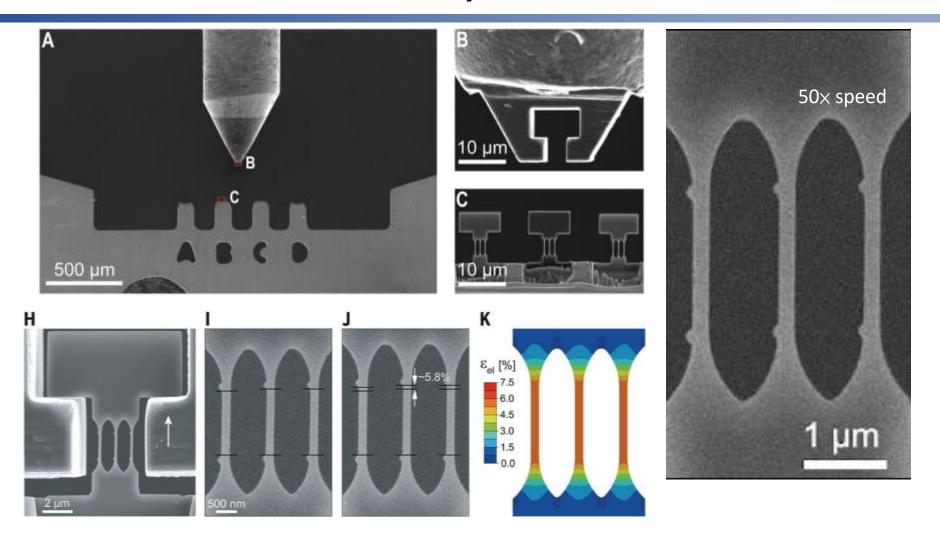


--- EELS by Yang Yang, Andy Minor @LBNL

Measured bandgap energy agrees well with the calculated bandgap decrease trend

"strained diamond" device

#### "Strained diamond" device array



Complete recover after being uniformly strained to ~5.8%, fractured at ~6% Diamond array samples with multiple bridges (can be scalable)

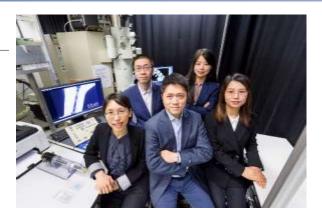
#### "Strained diamond" for future microelectronics/optoelectronics

#### Science

Science 01 Jan 2021: Vol. 371, Issue 6524, pp. 76-78 DOI: 10.1126/science.abc4174

# Achieving large uniform tensile elasticity in microfabricated diamond

Chaoqun Dang<sup>1</sup>\*, Jyh-Pin Chou<sup>1,2</sup>\*, Bing Dai<sup>3</sup>\*, Chang-Ti Chou<sup>4</sup>\*, Yang Yang<sup>5</sup>, Rong Fan<sup>1</sup>, Weitong Lin<sup>1</sup>, Fanling Meng<sup>6</sup>, Alice Hu<sup>1,7</sup>†, Jiaqi Zhu<sup>3</sup>†, Jiecai Han<sup>3</sup>, Andrew M. Minor<sup>5</sup>, Ju Li<sup>8</sup>†, Yang Lu<sup>1,7,9</sup>†

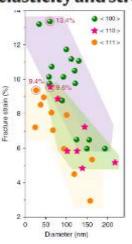




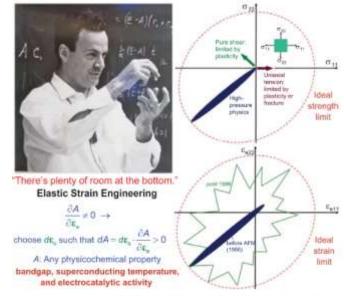
#### Pushing to the limit...



# Approaching diamond's theoretical elasticity and strength limits



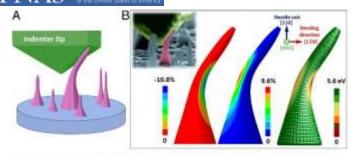
Nie et al. Nat. Commun. **10**, 5533 (2019)

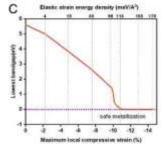


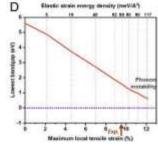
Li, Shan, Ma et al. MRS Bull. **39**, 108 (2014)

#### PHYSICAL REVIEW LETTERS 124, 147001 (2020)

#### Metallization of diamond







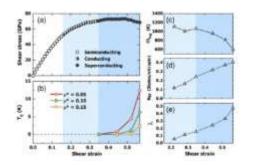
Shi et al. PNAS 116, 4117–4122 (2020)

#### Editors' Suggestion

#### Superconductivity in Compression-Shear Deformed Diamond

Chang Liu<sup>0</sup>, <sup>1</sup> Xianqi Song<sup>0</sup>, <sup>1</sup> Quan Li<sup>0</sup>, <sup>1,2,\*</sup> Yanming Ma<sup>0</sup>, <sup>1,2,\*</sup> and Changfeng Chen<sup>0,4</sup> <sup>1</sup> State Key Laboratory of Superhard Materials, Key Laboratory of Automobile Materials of MOE, Department of Materials Science, and Innovation Center for Computational Physics Method and Software, Jilin University, Changchun 130012, China

<sup>2</sup>International Center of Future Science, Jilin University, Changchun 130012, China
<sup>3</sup>Department of Physics and Astronomy, University of Nevada, Las Vegas, Nevada 89154, USA



#### A new diamond age...



#### MOTHERBOARD

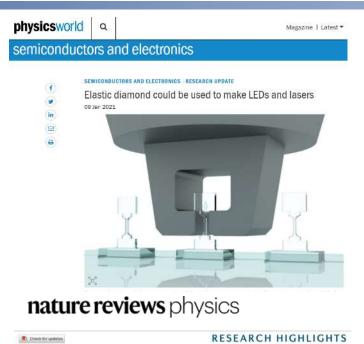
### Scientists Are Stretching Diamonds to Revolutionize Electronics

Researchers are breaking down diamonds to nano-size and physically stretching them. The eventual results could change everything we know about electronics.



Long story short, if these findings remain consistent, we're sitting pretty for the next ten years of optoelectronics.

While that's a few years out, "The Dawn of a Diamond Age of Electronics," <u>as</u> one industry pioneer puts it, is upon us.





Nature Reviews Physics | https://doi.org/10.1038/s42254-021-00279-5 | Published online: 13 January 2021

minion has a very mig carrier mobility and thermal conductivity which would make it ideal for electronic devices, were it not for the very large electronic band gap of 5.5°C, which effectively makes diamond an insulator. As diamond is an incredibly hard material, modifying its mechanical properties is a challenge. Now, writing in Science, Chaoqun Dang

and colleagues, demonstrate the ability to stretch diamond by up to 9%. Supporting density functional theory calculations show that such elastic strain engineering can make diamond semiconducting.

diamond semiconducting.

Although diamond has been strained before, this has been done by flexural bending (like jumping on a rope bridge) which has led to non-uniform strain. In this

experiment, Dang et al. stretched the diamond instead. They created micro-scale "bridges" of diamond and then gripped the ends with tiny pincers and pulled to stretch out along the length of the sample. The diamond completely recovered its original length after strain values of up to 9%. The elasticity depended on the crystal orientation of the direction of strain.

These experiments were followed up with density functional theory calculations to model how the electronic band gap changed as a function of strain. At 9% strain, the calculations show the bandgap reducing to 3.09 eV. This would turn diamond into a direct bandgap semiconductor, making it comparable to GaN or ZnO. The demonstration that diamond can be stretched opens up many possibilities. However, challenges remain, including making electronic measurements of the stretched diamond, sustaining the strain for long periods of time and finally integrating the stretched diamond







